

ABSTRACT OF THE DISCLOSURE

A trench gate type semiconductor device has an ON resistance that has been reduced. The device has a drain electrode on one side of the substrate and has a drift region, channel region, source region, and a source electrode on the other side. The channel region is sandwiched between a trench gate region covered with insulating film. Current passes when a positive bias voltage is applied to the trench region, and current is cut off when a negative bias voltage is applied.

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